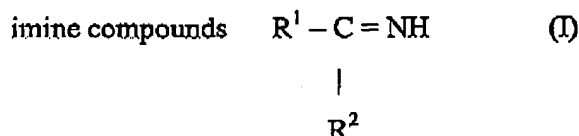


In the Claims:

1. (Previously presented) A polishing fluid useful for polishing tantalum-containing barrier materials of a semiconductor substrate comprising:

a nitrogen-containing compound having at least two nitrogen atoms comprising at least one of a compound of a formula selected from the group comprising:



and hydrazine compounds $\text{R}^3\text{R}^4\text{N} - \text{N}\text{R}^5\text{R}^6$ (II),

wherein R^1 comprises -H or -NH₂ and R^2 , R^3 , R^4 , R^5 and R^6 independently comprise substituents selected from the group consisting of -H, a hydrocarbon group, an amino group, a carbonyl group, an imido group, an azo group, a cyano group, a thio group, a seleno group and -OR⁷ where R^7 comprises a hydrocarbon group, and the nitrogen-containing compound being free of electron-withdrawing substituents; and the polishing fluid containing no abrasive particles and being capable of removing the tantalum-containing barrier materials from a surface of the semiconductor substrate.

2. Cancelled.

3. (Original) The polishing fluid of claim 1, wherein the nitrogen-containing compound contains the imine compound.

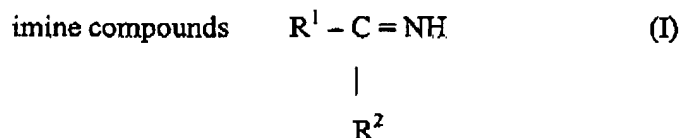
4. (Original) The polishing fluid of claim 1, wherein the nitrogen-containing compound contains the hydrazine compound.

5. (Previously presented) A polishing fluid useful for polishing tantalum-containing barrier materials of a semiconductor substrate comprising:

- 0 to 6 inhibitor for reducing the removal of an interconnect metal;
- 0 to 1 weight percent abrasive particles;
- 0 to 25 oxidizing agent;

0 to 15 complexing agent and

0.05 to 25 nitrogen-containing compound having at least two nitrogen atoms comprising at least one of a compound of a formula selected from the group comprising:



and hydrazine compounds $\text{R}^3\text{R}^4\text{N} - \text{N R}^5\text{R}^6$ (II);

wherein R^1 comprises -H or $-\text{NH}_2$ and R^2 , R^3 , R^4 , R^5 and R^6 independently comprise substituents selected from the group consisting of -H, a hydrocarbon group, an amino group, a carbonyl group, an imido group, an azo group, a cyano group, a thio group, a seleno group and $-\text{OR}^7$ where R^7 comprises a hydrocarbon group, and the nitrogen-containing compound having an electron-donating substituent; and the polishing fluid containing no abrasive particles and being capable of removing the tantalum-containing barrier materials from a surface of the semiconductor substrate.

6. (Previously presented) The polishing fluid of claim 5, wherein the polishing fluid has a pH between 7 and 12.

7. (Original) The polishing fluid of claim 5, wherein the nitrogen-containing compound contains the imine compound and the imine compound contains at least one selected from at least one of the group comprising 1,3-diphenyl guanidine, guanidine hydrochloride, tetramethylguanidine, formamidine acetate and acetamidine hydrochloride.

8. (Currently amended) The polishing fluid of claim 5, wherein the nitrogen-containing compound contains the hydrazine compound and the hydrazine compound contains at least one selected from at least one of the group comprising carbohydrazide, ~~imidazole~~, acetic hydrazide, semicarbazide hydrochloride, and formic hydrazide.

9 and 10 Cancelled.